

12A High-Speed MOSFET Drivers

Features

- · High Peak Output Current: 13A (typical)
- Low Shoot-Through/Cross-Conduction Current in Output Stage
- · Wide Input Supply Voltage Operating Range:
 - 4.5V to 18V
- High Continuous Output Current: 2.6A (max.)
- · Matched Fast Rise and Fall Times:
 - 21 ns with 10,000 pF Load
 - 42 ns with 22,000 pF Load
- Matched Short Propagation Delays: 44 ns (typ.)
- · Low Supply Current:
 - With Logic '1' Input 140 μA (typical)
 - With Logic '0' Input 40 μA (typical)
- Low Output Impedance: 0.9Ω (typical)
- Latch-Up Protected: Will Withstand 1.5A Output Reverse Current
- Input Will Withstand Negative Inputs Up To 5V
- Pin-Compatible with the TC4420/TC4429, TC4421/TC4422 and TC4421A/TC4422A MOSFET Drivers
- Space-Saving, Thermally-Enhanced, 8-Pin DFN Package

Applications

- · Line Drivers for Extra Heavily-Loaded Lines
- · Pulse Generators
- Driving the Largest MOSFETs and IGBTs
- · Local Power ON/OFF Switch
- · Motor and Solenoid Driver
- · LF Initiator

General Description

The TC4451/TC4452 are single-output MOSFET drivers. These devices are high-current buffer/drivers capable of driving large MOSFETs and Insulated Gate Bipolar Transistors (IGBTs). The TC4451/TC4452 have matched output rise and fall times, as well as matched leading and falling-edge propagation delay times. The TC4451/TC4452 devices also have very low crossconduction current, reducing the overall power dissipation of the device.

These devices are essentially immune to any form of upset, except direct overvoltage or over-dissipation. They cannot be latched under any conditions within their power and voltage ratings. These parts are not subject to damage or improper operation when up to 5V of ground bounce is present on their ground terminals. They can accept, without damage or logic upset, more than 1.5A inductive current of either polarity being forced back into their outputs. In addition, all terminals are fully protected against up to 4 kV of electrostatic discharge.

The TC4451/TC4452 inputs may be driven directly from either TTL or CMOS (3V to 18V). In addition, 300 mV of hysteresis is built into the input, providing noise immunity and allowing the device to be driven from slowly rising or falling waveforms.

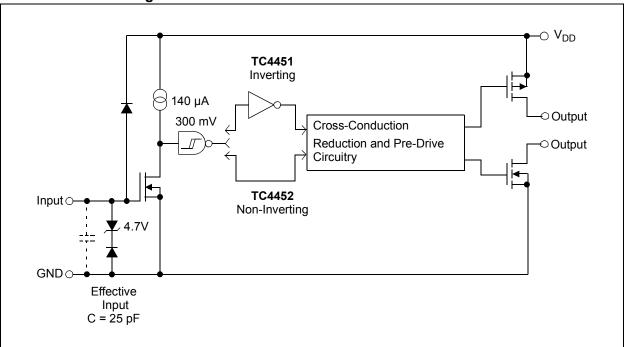
With both surface-mount and pin-through-hole packages, in addition to a wide operating temperature range, the TC4451/TC4452 family of 12A MOSFET drivers fit into most any application where high gate/line capacitance drive is required.

Package Types

8-Pin PDIP/SOIC(1, 2) TC4451 TC4452 V_{DD} 1 8 V_{DD} V_{DD} 1 ● 8 V_{DD} Z OUTPUT 6 OUTPUT INPUT 2 7 OUTPUT INPUT 2 NC 3 NC 3 6 OUTPUT 5 GND GND 4 5 GND GND 4 8-Pin DFN^(1, 2) TC4451 TC4452 V_{DD} 1 ° OUTPUT INPUT 2 OUTPUT 9 9 9 NC OUTPUT OUTPUT GND 4 GND 5-Pin TO-220^(1, 2) TC4451 TC4452 Tab is Common to $V_{\mbox{\scriptsize DD}}$ \bigcirc **Note 1:** Duplicate pins must both be connected for proper operation.

2: Exposed Thermal Pad (EP) of the DFN package is electrically isolated; see Table 3-1.

Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Supply Voltage $(V_{DD} + 0.3V)$ to (GND - 5V)Input Current $(V_{IN} > V_{DD})$50 mA † Notice: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Input							
Logic '1', High Input Voltage	V _{IH}	2.4	1.5	_	V		
Logic '0', Low Input Voltage	V_{IL}	_	1.3	0.8	V		
Input Current	I _{IN}	-10		+10	μΑ	$0V \le V_{IN} \le V_{DD}$	
Input Voltage	V _{IN}	– 5	_	$V_{DD} + 0.3$	V		
Output							
High Output Voltage	V _{OH}	$V_{DD} - 0.025$		_	V	DC Test	
Low Output Voltage	V _{OL}		I	0.025	V	DC Test	
Output Resistance, High	R _{OH}		1.0	1.5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Output Resistance, Low	R _{OL}		0.9	1.5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Peak Output Current	I _{PK}		13	_	Α	V _{DD} = 18V	
Continuous Output Current	I _{DC}	2.6	I	_	Α	$10V \le V_{DD} \le 18V$ (Note 2, Note 3)	
Latch-Up Protection Withstand Reverse Current	I _{REV}	_	>1.5	_	Α	Duty cycle \leq 2%, t \leq 300 μ s	
Switching Time (Note 1)		•					
Rise Time	t _R	_	30	40	ns	Figure 4-1 , C _L = 15,000 pF	
Fall Time	t _F	_	32	40	ns	Figure 4-1 , C _L = 15,000 pF	
Propagation Delay Time	t _{D1}		44	52	ns	Figure 4-1 , C _L = 15,000 pF	
Propagation Delay Time	t _{D2}	_	44	52	ns	Figure 4-1 , C _L = 15,000 pF	
Power Supply							
Power Supply Current	IS	_	140	200	μA	V _{IN} = 3V	
		_	40	100	μA	V _{IN} = 0V	
Operating Input Voltage	V_{DD}	4.5		18.0	V		
V _{DD} Ramp Rate	SV _{DD}	0.2	_	_	V/ms		

- Note 1: Switching times ensured by design.
 - 2: Tested during characterization, not production tested.
 - 3: Valid for AT and MF packages only. $T_A = +25$ °C.

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise noted, over operating temperature range with 4.5V \leq V _{DD} \leq 18V.							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Input							
Logic '1', High Input Voltage	V_{IH}	2.4	_	_	V		
Logic '0', Low Input Voltage	V_{IL}	_	_	0.8	V		
Input Current	I _{IN}	-10	_	+10	μA	$0V \le V_{IN} \le V_{DD}$	
Output							
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	_	V	DC Test	
Low Output Voltage	V _{OL}	_	_	0.025	V	DC Test	
Output Resistance, High	R _{OH}	_	_	2.2	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Output Resistance, Low	R _{OL}	_	_	2.0	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Switching Time (Note 1)							
Rise Time	t _R	_	35	60	ns	Figure 4-1 , C _L = 15,000 pF	
Fall Time	t _F	_	38	60	ns	Figure 4-1 , C _L = 15,000 pF	
Propagation Delay Time	t _{D1}	_	55	65	ns	Figure 4-1 , C _L = 15,000 pF	
Propagation Delay Time	t _{D2}	_	55	65	ns	Figure 4-1 , C _L = 15,000 pF	
Power Supply							
Power Supply Current	I _S	_	200	400	μA	V _{IN} = 3V	
		_	50	150	μA	V _{IN} = 0V	
Operating Input Voltage	V_{DD}	4.5	_	18.0	V		
V _{DD} Ramp Rate	SV _{DD}	0.2	_	_	V/ms		

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$.						
Parameters	Sym	Min	Тур	Max	Units	Conditions
Temperature Ranges						
Specified Temperature Range (V)	T _A	-40	_	+125	°C	
Maximum Junction Temperature	TJ	_	_	+150	°C	
Storage Temperature Range	T _A	-65	_	+150	°C	
Package Thermal Resistances						
Thermal Resistance, 5L-TO-220	θ_{JA}	_	39.5	_	°C/W	Without heat sink
Thermal Resistance, 8L-6x5 DFN	θ_{JA}	_	35.7	_	°C/W	Typical 4-layer board with vias to ground plane
Thermal Resistance, 8L-PDIP	θ_{JA}	_	89.3	_	°C/W	
Thermal Resistance, 8L-SOIC	$\theta_{\sf JA}$	_	149.5	_	°C/W	

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

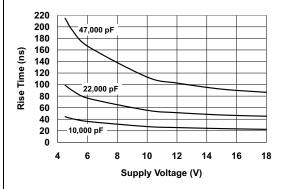


FIGURE 2-1: Rise Time vs. Supply Voltage.

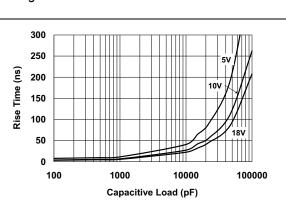


FIGURE 2-2: Rise Time vs. Capacitive Load.

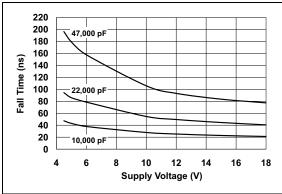


FIGURE 2-3: Fall Time vs. Supply Voltage.

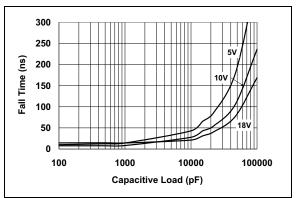


FIGURE 2-4: Fall Time vs. Capacitive Load.

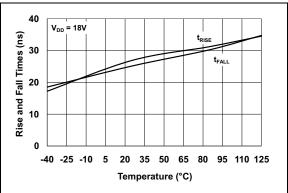


FIGURE 2-5: Rise and Fall Times vs. Temperature.

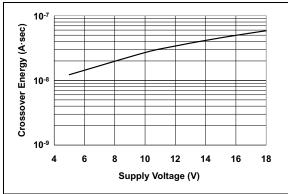


FIGURE 2-6: Crossover Energy vs. Supply Voltage.

Note: Unless otherwise indicated, T_A = +25°C with 4.5V \leq V_{DD} \leq 18V.

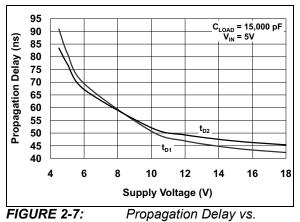
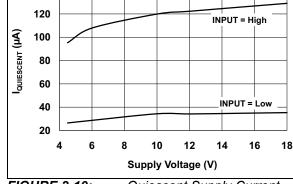


FIGURE 2-7: Supply Voltage.



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FIGURE 2-10: Quiescent Supply Current vs. Supply Voltage.

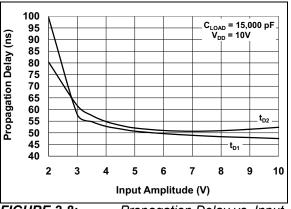


FIGURE 2-8: Propagation Delay vs. Input Amplitude.

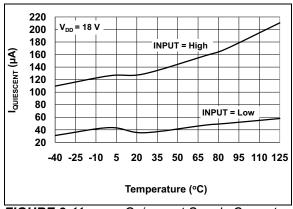


FIGURE 2-11: Quiescent Supply Current vs. Temperature.

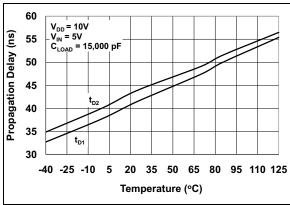


FIGURE 2-9: Propagation Delay vs. Temperature.

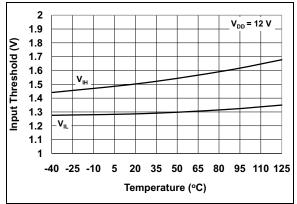


FIGURE 2-12: Input Threshold vs. Temperature.

Note: Unless otherwise indicated, T_A = +25°C with 4.5V \leq V_{DD} \leq 18V.

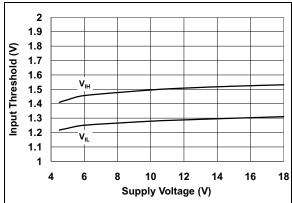


FIGURE 2-13: Input Threshold vs. Supply Voltage.

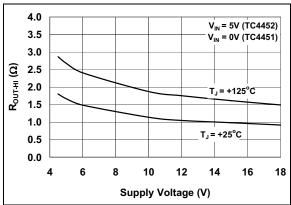


FIGURE 2-14: High-State Output Resistance vs. Supply Voltage.

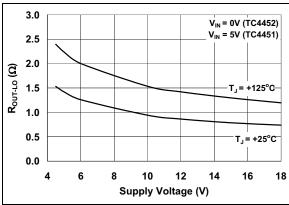


FIGURE 2-15: Low-State Output Resistance vs. Supply Voltage.

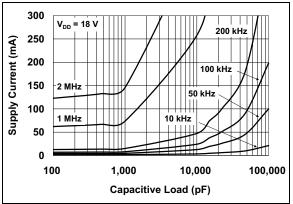


FIGURE 2-16: Supply Current vs. Capacitive Load ($V_{DD} = 18V$).

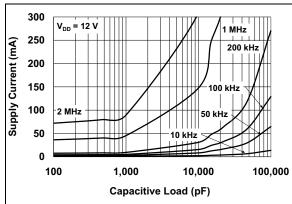


FIGURE 2-17: Supply Current vs. Capacitive Load ($V_{DD} = 12V$).

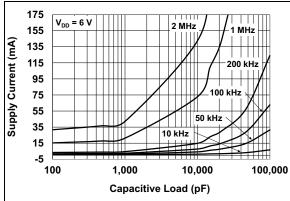


FIGURE 2-18: Supply Current vs. Capacitive Load ($V_{DD} = 6V$).

Note: Unless otherwise indicated, T_A = +25°C with 4.5V \leq V_{DD} \leq 18V.

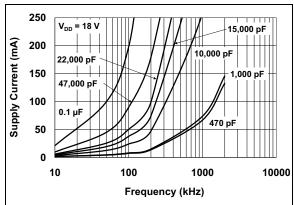


FIGURE 2-19: Supply Current vs. Frequency $(V_{DD} = 18V)$.

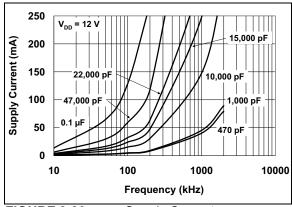


FIGURE 2-20: Supply Current vs. Frequency $(V_{DD} = 12V)$.

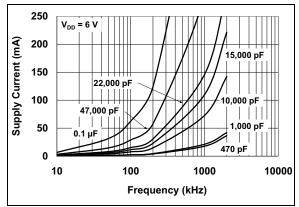


FIGURE 2-21: Supply Current vs. Frequency $(V_{DD} = 6V)$.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

8-Pin PDIP, SOIC	8-Pin DFN	5-Pin TO-220	Symbol	Description
1	1	_	V_{DD}	Supply input, 4.5V to 18V
2	2	1	INPUT	Control input, TTL/CMOS-compatible input
3	3	_	NC	No connection
4	4	2	GND	Ground
5	5	4	GND	Ground
6	6	5	OUTPUT	CMOS push-pull output
7	7	_	OUTPUT	CMOS push-pull output
8	8	3	V_{DD}	Supply input, 4.5V to 18V
_	9	_	EP	Exposed metal pad
_	_	TAB	V_{DD}	Metal tab is at the V _{DD} potential

3.1 Supply Input (V_{DD})

The V_{DD} input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pin. The V_{DD} input should be bypassed to ground with a local ceramic capacitor. The value of the capacitor should be chosen based on the capacitive load that is being driven. A minimum value of 1.0 μ F is suggested.

3.2 Control Input (INPUT)

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

3.3 CMOS Push-Pull Output (OUTPUT)

The MOSFET driver output is a low-impedance, CMOS, push-pull style output capable of driving a capacitive load with 12A peak currents. The MOSFET driver output is capable of withstanding 1.5A peak reverse currents of either polarity.

3.4 Ground (GND)

The ground pins are the return path for the bias current and for the high peak currents that discharge the load capacitor. The ground pins should be tied into a ground plane or have very short traces to the bias supply source return.

3.5 Exposed Metal Pad (EP)

The exposed metal pad of the 6x5 DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a Printed Circuit Board (PCB) to aid in heat removal from the package.

3.6 Metal Tab

The metal tab of the TO-220 package is connected to the V_{DD} potential of the device. This connection to V_{DD} can be used as a current carrying path for the device.

4.0 APPLICATIONS INFORMATION

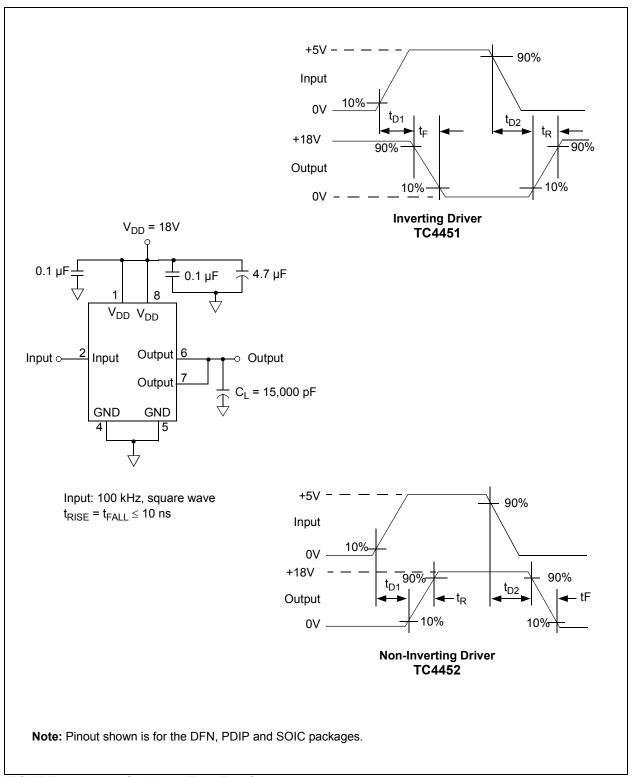
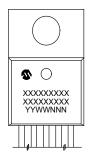


FIGURE 4-1: Switching Time Test Circuits.

5.0 PACKAGING INFORMATION

5.1 Package Marking Information

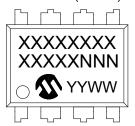
5-Lead TO-220



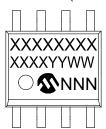
8-Lead DFN-S (6x5x0.9 mm)



8-Lead PDIP (300 mil)



8-Lead SOIC (3.90 mm)



Example:



Example:



Example



Example



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

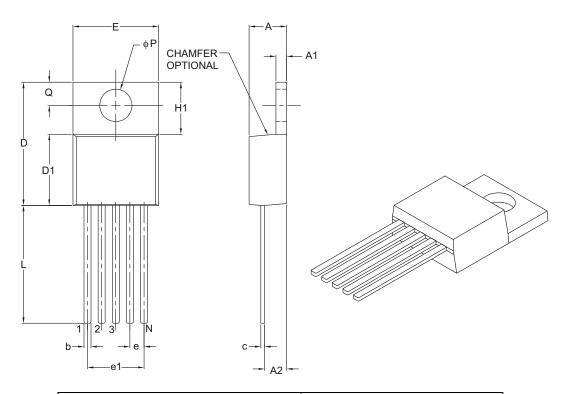
e3 Pb-free JEDEC designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

5-Lead Plastic Transistor Outline (AT) [TO-220]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	INCHES		
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N		5	
Pitch	е		.067 BSC	
Overall Pin Pitch	e1		.268 BSC	
Overall Height	A	.140	_	.190
Overall Width	E	.380	_	.420
Overall Length	D	.560	_	.650
Molded Package Length	D1	.330	_	.355
Tab Length	H1	.204	_	.293
Tab Thickness	A1	.020	_	.055
Mounting Hole Center	Q	.100	_	.120
Mounting Hole Diameter	φР	.139	_	.156
Lead Length	L	.482	_	.590
Base to Bottom of Lead	A2	.080	_	.115
Lead Thickness	С	.012	_	.025
Lead Width	b	.015	.027	.040

Notes:

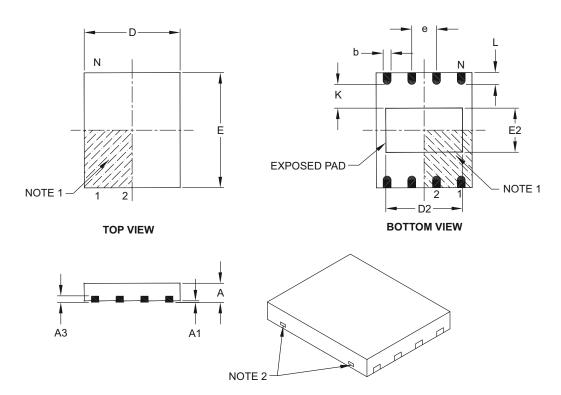
- 1. Dimensions D and E do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .005" per side.
- 2. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-036B

8-Lead Plastic Dual Flat, No Lead Package (MF) - 6x5 mm Body [DFN-S]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS		
Dimensio	n Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		1.27 BSC	
Overall Height	Α	0.80 0.85 1.00		
Standoff	A1	0.00 0.01 0.05		
Contact Thickness	А3	0.20 REF		
Overall Length	D	5.00 BSC		
Overall Width	Е		6.00 BSC	
Exposed Pad Length	D2	3.90	4.00	4.10
Exposed Pad Width	E2	2.20 2.30 2.40		
Contact Width	b	0.35 0.40 0.48		
Contact Length	L	0.50 0.60 0.75		
Contact-to-Exposed Pad	K	0.20	_	_

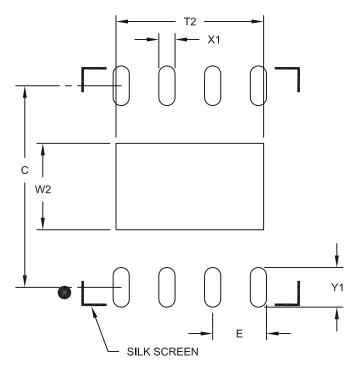
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Package is saw singulated.
- 4. Dimensioning and tolerancing per ASME Y14.5M.
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 - REF: Reference Dimension, usually without tolerance, for information purposes only.

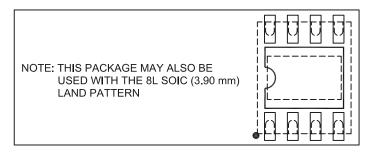
Microchip Technology Drawing C04-122B

8-Lead Plastic Dual Flat, No Lead Package (MF) - 6x5 mm Body [DFN-S]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN



	MILLIMETERS			
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E	1.27 BSC		
Optional Center Pad Width	W2			2.40
Optional Center Pad Length	T2			4.10
Contact Pad Spacing	С		5.60	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.10

Notes:

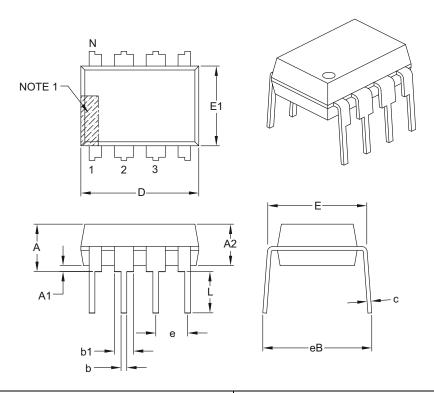
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2122A

8-Lead Plastic Dual In-Line (PA) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	INCHES		
	Dimension Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		.100 BSC	
Top to Seating Plane	Α	_	_	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	_	_
Shoulder to Shoulder Width	E	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.348	.365	.400
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	С	.008	.010	.015
Upper Lead Width	b1	.040	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eB	-	_	.430

Notes:

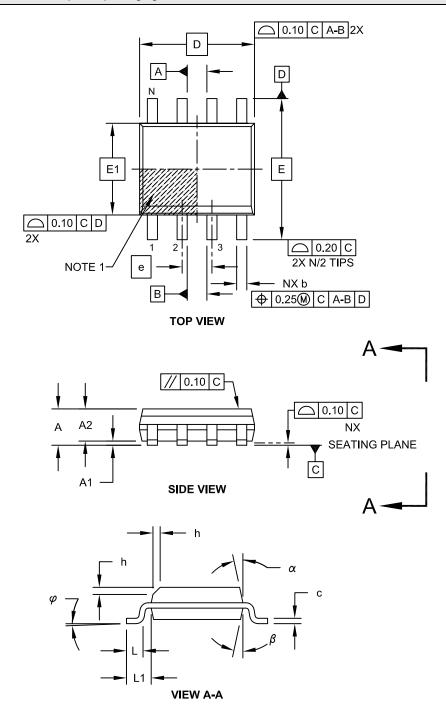
- 1. Pin 1 visual index feature may vary, but must be located with the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm Body [SOIC]

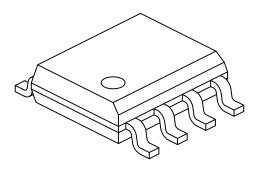
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing No. C04-057C Sheet 1 of 2

8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Number of Pins	Ν		8	
Pitch	е		1.27 BSC	
Overall Height	Α	1	ı	1.75
Molded Package Thickness	A2	1.25	ı	-
Standoff §	A1	0.10	ı	0.25
Overall Width	E	6.00 BSC		
Molded Package Width	E1	3.90 BSC		
Overall Length	D	4.90 BSC		
Chamfer (Optional)	h	0.25	ı	0.50
Foot Length	L	0.40	ı	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0° - 8°		8°
Lead Thickness	С	0.17 - 0.25		0.25
Lead Width	b	0.31	ı	0.51
Mold Draft Angle Top	α	5°	=	15°
Mold Draft Angle Bottom	β	5°	-	15°

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M

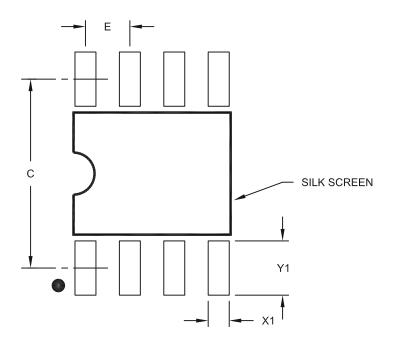
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing No. C04-057C Sheet 2 of 2

8-Lead Plastic Small Outline (OA) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	Dimension Limits			MAX
Contact Pitch	Е	1.27 BSC		
Contact Pad Spacing	C	5.40		
Contact Pad Width (X8)	X1	0.60		0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

NOTES:

APPENDIX A: REVISION HISTORY

Revision B (March 2012)

The following is the list of modifications:

- Added V_{DD} Ramp Rate value in both DC Characteristics and DC Characteristics (Over Operating Temperature Range) tables.
- 2. Updated package thermal resistances values in Temperature Characteristics table.
- Updated package specification drawings in Section 5.0, Packaging Information to show all available drawings.

Revision A (February 2006)

Original release of this document.

NOTES:

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. X	PART NO. X XX XXX			
 Device Tempe Ran	rature Package Tape & Reel ge	a)	TC4451VAT:	12A High-Speed Inverting MOSFET Driver, TO-220 package
Device:	TC4451: 12A High-Speed MOSFET Driver, Inverting TC4452: 12A High-Speed MOSFET Driver, Non-Inverting	b)	TC4451VOA:	12A High-Speed Inverting MOSFET Driver, SOIC package
Temperature Range:	V = -40°C to +125°C	c)	TC4451VMF:	12A High-Speed Inverting MOSFET Driver, DFN package
Package: *	AT = TO-220, 5-lead MF = Dual, Flat, No-Lead (6x5 mm Body), 8-lead MF713 = Dual, Flat, No-Lead (6x5 mm Body), 8-lead	a)	TC4452VPA:	12A High-Speed Non-Inverting MOSFET Driver, PDIP package
	(Tape and Reel) PA = Plastic DIP (300 mil Body), 8-lead OA = Plastic SOIC (150 mil Body), 8-lead OA713 = Plastic SOIC (150 mil Body), 8-lead (Tape and Reel)	b)	TC4452VOA:	12A High-Speed Non-Inverting MOSFET Driver, SOIC package
	*All package offerings are Pb Free (Lead Free).	c)	TC4452VMF:	12A High-Speed Non-Inverting MOSFET Driver, DFN package

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Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
 knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
 Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

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ISBN: 978-1-62076-077-2

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